MAAVSS0006

3 Volt Voltage Variable Attenuator 25 dB, DC-2.5 GHz

V1

Features

- Single Voltage Control: 0 to -3 Volts
- 25 dB Attenuation Range at 0.9 GHz
- Low DC Power Consumption
- Lead-Free SOT-25 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free "Green" Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of AT-255

Description

M/A-COM's MAAVSS0006 is a GaAs MMIC voltage variable absorptive attenuator in a lead-free SOT-25 surface mount plastic package. The MAAVSS0005 is ideally suited for use where variable attenuation, fine tuning, and very low power consumption are required.

Typical applications include radio, cellular, GPS equipment and automatic gain/level control circuits.

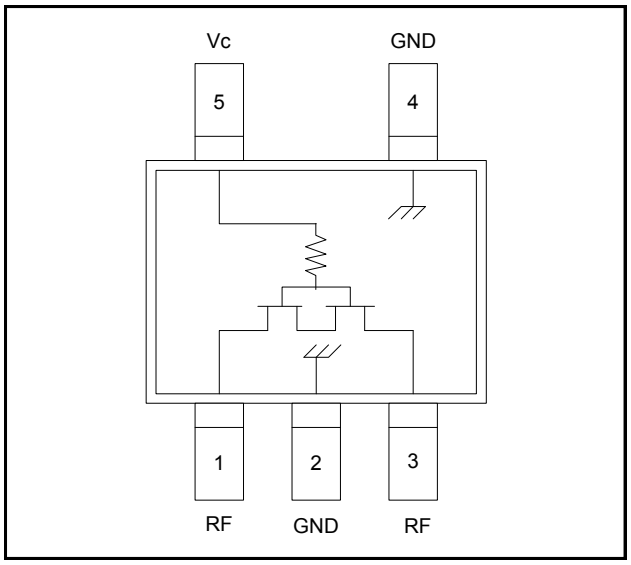
The MAAVSS0006 is fabricated using a mature 1-micron GaAs MESFET process. The process features full chip passivation for increased performance and reliability.

Ordering Information

Part Number	Package
MAAVSS0006	Bulk Packaging
MAAVSS0006TR-3000	3000 piece reel
MAAVSS0006SMB	Sample Board

1. Reference Application Note M513 for reel size information.
2. All sample boards include 5 loose parts.

Functional Schematic [1]



3. V_C = -3 V to 0 V @ 25 µA maximum.

Pin Configuration

Pin No.	Function	Pin No.	Function
1	RF Port	4	Ground
2	Ground	5	V_C
3	RF Port		

Absolute Maximum Ratings [2,3]

Parameter	Absolute Maximum
Input Power	+21 dBm
Control Voltage V_C	-8 V ≤ Vc ≤ +0.5 V
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

4. Exceeding any one or combination of these limits may cause permanent damage to this device.
5. MA-COM does not recommend sustained operation near these survivability limits.

* Restrictions on Hazardous Substances, European Directive 2002/95/EC.

3 Volt Voltage Variable Attenuator 25 dB, DC-2.5 GHz

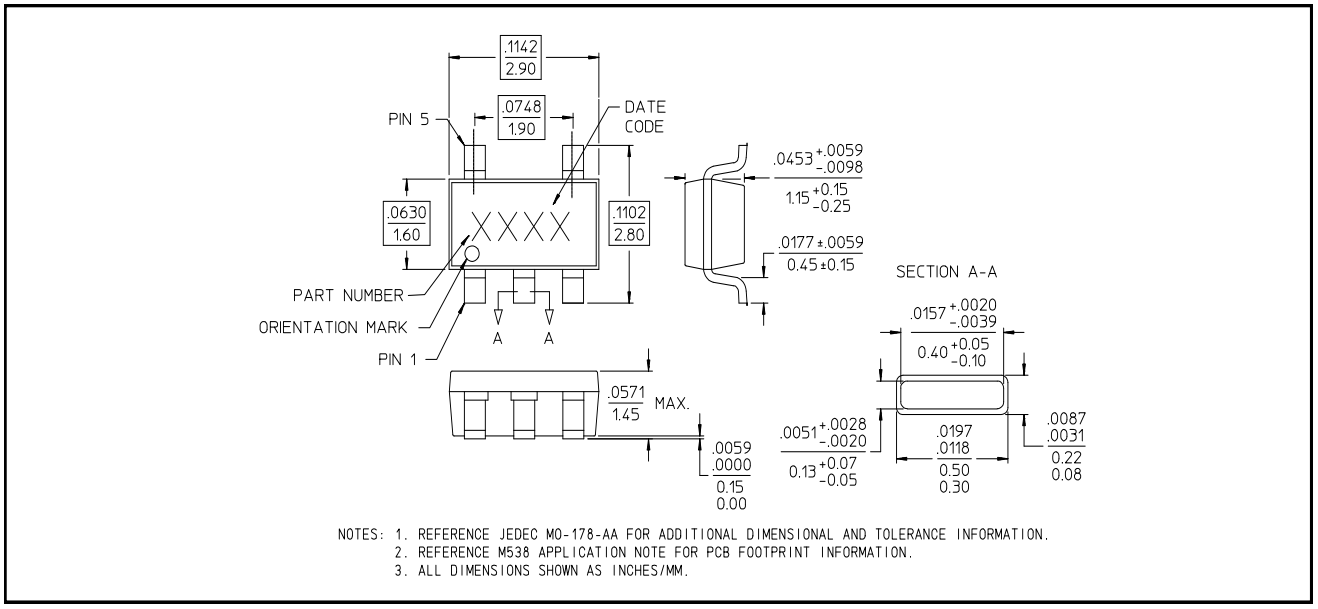
V1

Electrical Specifications: T_A = 25°C, Z_0 = 50 Ω

Parameter	Test Conditions	Units	Min	Typ	Max
Insertion Loss[5]	DC - 2.0 GHz	dB	—	3.6	4.2
Attenuation	DC - 1.0 GHz 1.0 - 2.0 GHz	dB dB	23 18	25 20	— —
Flatness (Peak-to-Peak)	0.5 - 1.0 GHz 1.0 - 2.0 GHz	dB dB	— —	± 7 ± 5	± 10 ± 8
VSWR	DC - 2.0 GHz	Ratio	—	3:1	—
Trise, Tfall	10% to 90% RF, 90% to 10% RF	nS	—	10	—
Ton, Toff	50% Control to 90% RF, 50% Control to 10% RF	nS	—	20	—
Transients	In Band	mV	—	10	—

5. Insertion loss varies 0.003 dB/°C.

Lead-Free SOT-25†



† Reference Application Note M538 for lead-free solder reflow recommenda-

Meets JEDED moisture Sensitivity Level 1 requirements

Handling Procedures

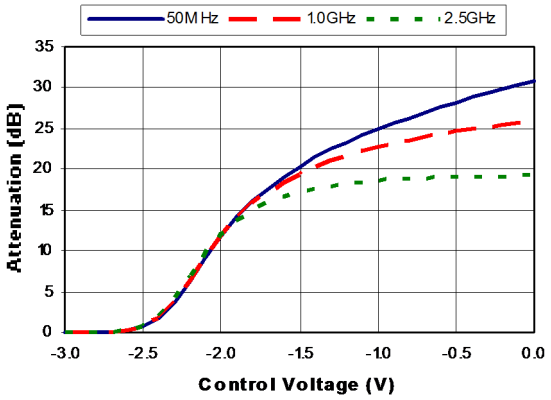
Please observe the following precautions to avoid damage:

Static Sensitivity

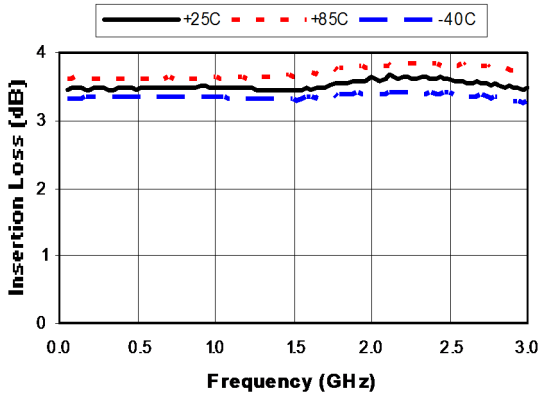
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Typical Performance Curves

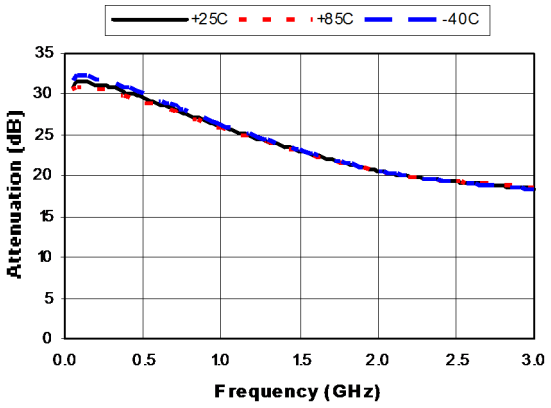
Relative Attenuation vs. Control Voltage



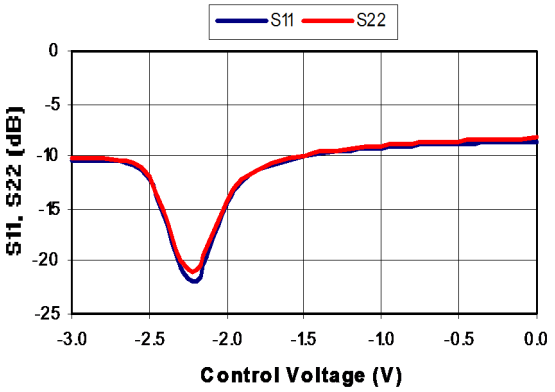
Insertion Loss vs. Frequency



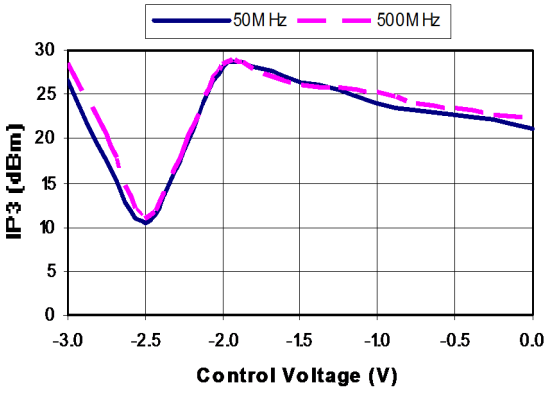
Maximum Relative Attenuation vs. Frequency



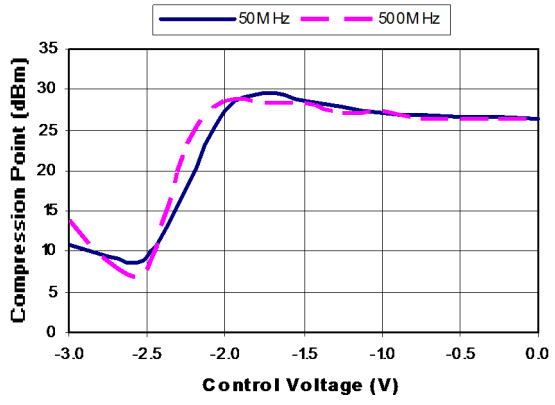
Return Loss vs. Control Voltage @ 900 MHz



Input IP3 vs. Control Voltage



Input P1dB vs. Control Voltage



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Attenuators ***category:***

Click to view products by MACOM ***manufacturer:***

Other Similar products are found below :

MACOM